

Appl. No. 10/627,609
Amendment dated: August 22, 2005
Reply to OA of: May 25, 2005

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1(canceled).

2(canceled).

3(canceled).

4(canceled).

5(canceled).

6(canceled).

7(canceled).

8(canceled).

9(canceled).

10(canceled).

11(canceled).

12(canceled).

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13(original). A fabrication method of a circuit substrate, comprising:
providing a board;
forming a via in the board;
forming a metal layer on an inner wall of the via;
cutting the via to form a cutting street to separate the metal layer into a plurality of separated metal layers; and
filling an insulator in the via and the cutting street.

14(original). The fabrication method of a circuit substrate of claim 13, further comprising:
forming a via land on the board and at the periphery of the via.

15(original). The fabrication method of a circuit substrate of claim 14, wherein cutting the via further separates the via land into a plurality of separated via lands.

16(original). The fabrication method of a circuit substrate of claim 13, wherein the via is a through hole.

17(canceled).

18(original). The fabrication method of a circuit substrate of claim 13, wherein the via is a blind via.

19(original). The fabrication method of a circuit substrate of claim 13, wherein the material of the metal layer is copper.

20(original). The fabrication method of a circuit substrate of claim 13, wherein the material of the insulator layer is epoxy.

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21(original). The fabrication method of a circuit substrate of claim 13, wherein the material of the insulator layer is ink.

22(previously presented). The fabrication method of a circuit substrate of claim 13, wherein the board comprises a plurality of insulating layers and conductive trace layers, and the insulating layers are interlaced with the conductive trace layers.

23(original). The fabrication method of a circuit substrate of claim 13, wherein forming the metal layer on the inner wall of the via comprises:

forming an activated film on the inner wall of the via by electro-less plating; and
forming a metal film on the activated film by plating.

24(original). The fabrication method of a circuit substrate of claim 23, wherein the activated film comprises a conductive polymer film.

25(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises mechanical drilling.

26(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises laser ablation.

27(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises photochemical reaction.

28(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises plasma etching.